FSUSB242 Type-C USB Port **Protection Switch**

Features

- Fully USB Data Port Protection
- V_{DD} 0 V- 5.5 V (12 V DC tolerant)
- -18 V to +20 V DC Tolerance on HSD± Port
- ±25 V IEC 64000-4-5 Surge Protection w/o External TVS
- V_{DD} Operating Range, 2.7 V-5.5 V
- HSD RON: 5 Ω Typical
- C_{ON} = 5 pF Typical
- Wide –3 dB Bandwidth: > 720 MHz
- Low Power Operation: I_{CC} < 10 μA (Typical)
- Over Voltage Protection: 3.6 V & 4.5 V

Typical Applications

- Smartphones
- Tablets
- Laptops

Safety Mechanisms Highlight

- 3.6 V & 4.5 V OVP Trip Point
- ±25 V Surge Protection without Need for External TVS







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WLCSP9 1.20 × 1.20 CASE 567UL

MARKING DIAGRAM



- MT = Specific Device Code
- &K = 2 Digit Lot Run Code х
 - = Year
- = 2 Week Data Code Y
- 7 = Plant Code

PIN CONNECTION



TOP Through View

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.



Figure 2. Simplified Block Diagram

Table 1. PIN FUNCTION DESCRIPTION

CSP Bump	Name	Туре	Description	
A1	VDD	Power	Supply Power	
B1	GND	Ground	Ground	
A3	HSD+	Data	Common High Speed Data Bus	
A2	HSD-	Data	Common High Speed Data Bus	
B3	HSD1+	Data	Multiplexed High Speed Data Port 1	
C3	HSD1-	Data	Multiplexed High Speed Data Port 1	
C2	HSD2+	Data	Multiplexed High Speed Data Port 2	
C1	HSD2-	Data	Multiplexed High Speed Data Port 2	
B2	SEL	I/O	Tri-Input HSD Switch Select & /OE	

Table 2. SWITCH TRUTH TABLE CONFIGURATION

VDD	SEL	Switch Configuration		
UVLO	X Switch off High impedance			
Valid	0	HSD+ = HSD1+, HSD- = HSD1-		
Valid	1	HSD+ = HSD2+, HSD- = HSD2-		
Valid	Float/High-Z	Switch Disable High impedance		

APPLICATION INFORMATION

Over Voltage Protection

Over voltage protection turns the switch off if the inputs HSD+/HSD- rise above the over voltage trip threshold.

Under Voltage Lockout

The under–voltage lockout on V_{DD} pin turns the switch off if the V_{DD} voltage drops below the lockout threshold. With the SELpin active, the input voltage rising above the UVLO threshold releases the lockout and enables the switch.

Tri-State Input Control Pin (SEL)

The SEL pin can be tri-stated to disable the switch to save power, there are a few ways to achieve this. If the SEL pin is controlled by GPIO in the system, if the GPIO pin has a High-Z state where the impedance of the High-Z state is larger then 2 M Ω the switch will recognize the High–Z state and disable the switch. If the system does not have GPIO that supports High–Z state, the user can utilize 2 MOSFETs or a Logic Device to achieve the same result.

For GPIO

The SEL pin function below:

- If the input is pulled up with less than 50 k Ω it will be considered as Logic High
- If the input is pulled down with less than 50 kΩ it will be consider as Logic Low
- If the input is pulled up or down with more 4 M Ω it will be consider as float/High-Z

System Timing Diagram



Figure 3. System Timing Plot

USB High Speed Eye Diagram

 $V_{DD} = 5.5 V HSD$ to HSD1 Path



Figure 4. HS USB Eye @ V_{DD} = 5 V

 $V_{DD} = 2.7 V HSD$ to HSD2 Path



Figure 5. HS USB Eye @ V_{DD} = 2.7 V

Symbol	Par	ameter		Min	Max	Unit
V _{DD}	Supply Voltage from V _{DD}			-0.5	12.0	V
V _{SW}	DC Input voltage tolerance for HSD±,	to GND		-18	20	V
	DC Input voltage tolerance for HSD1±	nput voltage tolerance for HSD1 \pm , HSD2 \pm to GND				V
V _{CONTROL}	DC Input Voltage (SEL)	Input Voltage (SEL)				V
I _{SW}	DC HSD Switch Current		100	mA		
I _{IK}	DC Input Diode Current	-50		mA		
T _{STORAGE}	Storage Temperature Range	-65	+150	°C		
TJ	Maximum Junction Temperature		+150	°C		
ΤL	Lead Temperature (Soldering, 10 seco	onds)		+260	°C	
ESD	IEC 61000-4-2 System ESD	Connector Pins (HSD±)	Air Gap	15		kV
			Contact	8		
	Human Body Model, JEDEC	Power to GND		2		kV
	JESD22-A114	Internal Pin to GND (HSD	01±, HSD2±)	2		
		External Pin to GND (HSI	External Pin to GND (HSD±)			1
	Charged Device Model, JEDEC All Pins LESD22–C101			1		
IEC 61000-4-5 Surge Protectio		HSD±, to GND		±25		V
		V _{DD} to GND		+12		V

Table 3. ABSOLUTE MAXIMUM RATINGS

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
V _{DD}	Supply Voltage	2.7	4.2	5.5	V
V _{SW1}	HSD1 Switch I/O Signal Swing Voltage (Note 1)	-0.5		3.6	V
V _{SW2}	HSD2 Switch I/O Signal Swing Voltage (Note 1)	-0.5		4.5	V
I _{CCSW}	Maximum HSD Switch Continuous Current			75	mA
V _{CNTRL}	Control Input Voltage (SEL)	-0.5		V _{DD}	V
T _A	Operating Temperature	-40		+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond

The switch swing voltage is based on the OVP trip level, and when OVP triggers the switch will be disabled to protect the host and no longer in the standard operating condition, once over voltage is removed the device will automatically recover back to normal condition.

Table 5. DC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at $T_A = 25^{\circ}C$ and $V_{DD} = 4.2$ V unless otherwise specified.)

				T _A = −40 to +85°C T _J = −40 to +125°C					
Symbol	Characteristic	V _{DD} (V)	Conditions	Min	Тур	Max	Unit		
	BASIC OPERATION DEVICE								

BASIC OPERATION DEVICE

I _{CC}	Quiescent Supply Current	2.7 to 5.5	WLCSP: /OE = H & L, I _{OUT} = 0		10		μA
I _{OFF}	Power-Off Leakage Current	0	$V_{SWHSD1} = 0 V \text{ to } 3.6 V,$ $V_{SWHSD2} = 0 V \text{ to } 4.5 V$	-3		3	μΑ
I _{IN}	Control Input Leakage	2.7 to 5.5	V _{CNTRL} = 0 V to V _{DD}	-2		4	μA

Table 5. DC ELECTRICAL CHARACTERISTICS (continued)

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at $T_A = 25^{\circ}C$ and $V_{DD} = 4.2$ V unless otherwise specified.)

			T _A = −40 to +85°C T _J = −40 to +125°C				
Symbol	Characteristic	V _{DD} (V)	Conditions	Min	Тур	Max	Unit
BASIC OPE	RATION DEVICE		· · · · · ·				
I _{OZ}	Off State Leakage	2.7 to 5.5	$\label{eq:HSD} \begin{array}{l} HSD{\pm} \geq 0 \ V, \ HSD1{\pm}, \\ HSD2{\pm} \leq 3.6 \ V \end{array}$	-3		5	μΑ
BASIC OPE	ERATION HSD SWITCH		· · · · · ·				
R _{ON}	HSD Path On Resistance	2.7 to 5.5	I_{OUT} = 8 mA, V_{SW} = 0 V to 0.4 V		5		Ω
ΔR_{ON}	HSD Path Delta R _{ON}	2.7 to 5.5	I_{OUT} = 8 mA, V_{SW} = 0 V to 0.4 V		0.15		Ω
V _{IH}	SEL Input Voltage High	2.7 to 5.5		1.3			V
V_{IM}	SEL Input Voltage Middle (Note 2)	2.7 to 5.5		0.8		1.0	V
V_{IL}	SEL Input Voltage Low	2.7 to 5.5				0.5	V
Zfloat	Impedance to VDD or GND detected as a Float including $V_{DD} = 0$	2.7 to 5.5		2.5			MΩ
V _{OV_TRIP1}	Input OVP Lockout for HSD1	2.7 to 5.5	$V_{HSD\pm}$ Rising, SEL = 0	3.6	3.8	4	V
			$V_{HSD\pm}$ Falling, SEL = 0	3.3	3.5		
V _{OV_TRIP2}	Input OVP Lockout for HSD2	2.7 to 5.5	$V_{HSD\pm}$ Rising, SEL = 1	4.5	4.7	4.9	V
			V _{HSD±} Falling, SEL = 1	4.2	4.4		
V _{OV_HYS}	Input OVP Hysteresis	2.7 to 5.5			0.3		V
V _{NV_TRIP}	Input Negative Voltage Lockout	2.7 to 5.5	V _{HSD±} Falling		-1.0		V
			V _{HSD±} Rising		-0.7		
V _{NV_HYS}	Input OVP Hysteresis	2.7 to 5.5			0.3		V
V _{CL}	Clamping Voltage	2.7 to 5.5	$V_{HSD\pm} \ge V_{OV_TRIP}$		4.5		V
V _{UVLO}	Under-Voltage Lockout		V _{DD} Rising		2.4	2.7	V
			V _{DD} Falling		2.3		1
TSD	Thermal Shutdown (Note 2)		Shutdown Threshold		150		°C
			Return from Shutdown		130]
			Hysteresis		20		1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Guaranteed by characterization or Design, not production tested.

Table 6. AC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at $T_A = 25^{\circ}C$ and $V_{DD} = 4.2$ V unless otherwise specified.)

				T _A = −40 to +85°C T _J = −40 to +125°C			
Symbol	Characteristic	V _{DD} (V)	Conditions	Min	Тур	Max	Unit
HSD SWIT	CH TIMING PARAMETER						
t _{OVP}	OVP Response Time (Note 33)	2.7 to 5.5	$\begin{array}{l} I_{OUT} = 8 \text{ mA, } C_L = 5 \text{ pF,} \\ R_L = 50 \ \Omega, \ V_{HSD\pm} = 3.3 \text{ V to} \\ 4.9 \text{ V} \end{array}$		0.35		μs
t _{ON}	Turn-On Time, SEL to Output	2.7 to 5.5	$R_L = 50 \Omega$, $C_L = 5 pF$		0.1		ms
tOFF	Turn-Off Time, SEL to Output	2.7 to 5.5	$ \begin{array}{l} R_L = 50 \ \Omega, \ C_L = 5 \ pF, \\ V_{SW} = 0.8 \ V \end{array} $		0.2		μs
t _{PD}	Propagation Delay (Note 3)	2.7 to 5.5	$ \begin{array}{l} R_L = 50 \; \Omega, \; C_L = 5 \; pF, \\ V_{SW} = 0.8 \; V \end{array} $		1.3		ns
t _{BBM}	Break-Before-Make (Note 3)	2.7 to 5.5	$ \begin{array}{l} R_L = 50 \ \Omega, \ C_L = 5 \ pF, \\ V_{SW1} = V_{SW2} = 0.8 \ V \end{array} $		50		μs
t _{SK(P)}	Skew of Opposite Transitions of the Same Output (Note 3)	2.7 to 5.5	$\label{eq:VSW} \begin{array}{l} V_{SW} = 0.2 \; Vdiff_{PP}, \; R_{L} = 50 \; \Omega, \\ C_{L} = 5 \; pF \end{array}$		35		ps
tj	Total Jitter (Note 3)	2.7 to 5.5	$\begin{array}{l} V_{SW} = 0.2 \; Vdiff_{PP}, R_L = 50 \; \Omega, \\ C_L = 5 \; pF, \; t_R = t_F = 500 \; ps \\ (10 - 90\%) \; @ \; 480 \; Mbps \\ (PRBS = 2^{15} - 1) \end{array}$		250		ps
ISD± SWI	TCH CAPACITANCE						
0	Control Din Innut Consolitones	0			4 5		~

C _{IN}	Control Pin Input Capacitance (Note 3)	0		1.5	pF	
C _{ON}	HSD± On Capacitance (Note 3)	2.7 to 5.5	SEL = L/H, f = 240 MHz	4		
C _{OFF}	HSD± Off Capacitance (Note 3)	2.7 to 5.5	SEL = Float, f = 240 MHz	3		ĺ

HSD SWITCH BANDWIDTH

BW	-3dB SDD21 Bandwidth	2.7 to 5.5	$R_L = 50 \ \Omega, \ C_L = 0 \ pF$	1000	MHz
	(Note 3)		$R_L = 50 \Omega$, $C_L = 5 pF$	550	MHz

HSD SWITCH AC PARAMETER

O _{IRR}	Off Isolation (Note 3)	2.7 to 5.5	R_L = 50 Ω , f = 240 MHz	-35	dB
Xtalk	Non-Adjacent Channel Crosstalk (Note 3)	2.7 to 5.5	$R_L = 50 \ \Omega$, f = 240 MHz	-40	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Guaranteed by characterization or Design, not production tested.

TEST DIAGRAMS



Figure 6. On Resistance



**Each switch port is tested separately

Figure 7. Off Leakage



 R_L , R_S , and C_L are functions of the application environment (see AC Tables for specific values) C_L includes test fixture and stray capacitance.





Figure 9. Turn-On / Turn-Off Waveforms



Figure 10. Propagation Delay (t_Rt_F – 500 ps)



Figure 11. Intra-Pair Skew Test t_{SK(P)}

TEST DIAGRAMS (Continued)



Figure 12. Break-Before-Make Interval Timing



Figure 13. Bandwidth





Figure 15. Non-Adjacent Channel-to-Channel Crosstalk

TEST DIAGRAMS (Continued)







Figure 17. Channel On Capacitance

ORDERING INFORMATION

Table 7. AVAILABLE PART NUMBERS

Part Number	Device Code	Operating Temperature Range	Package	Packing Method†
FSUSB242UCX	МТ	−40 to 85°C	9-Ball WLCSP (1.20 x 1.20 mm)	Tape and Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PACKAGE DIMENSIONS

WLCSP9, 1.2x1.2x0.48 CASE 567UL ISSUE A



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